

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N4001GPP SERIES

GLASS PASSIVATED JUNCTION
SILICON RECTIFIER
1.0 AMP, 50 THRU 1000 VOLTS

JEDEC DO-41 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N4001GPP Series types are 1.0 Amp Glass Passivated Junction Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for use in all types of military, commercial, industrial, entertainment, computer, and automotive applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

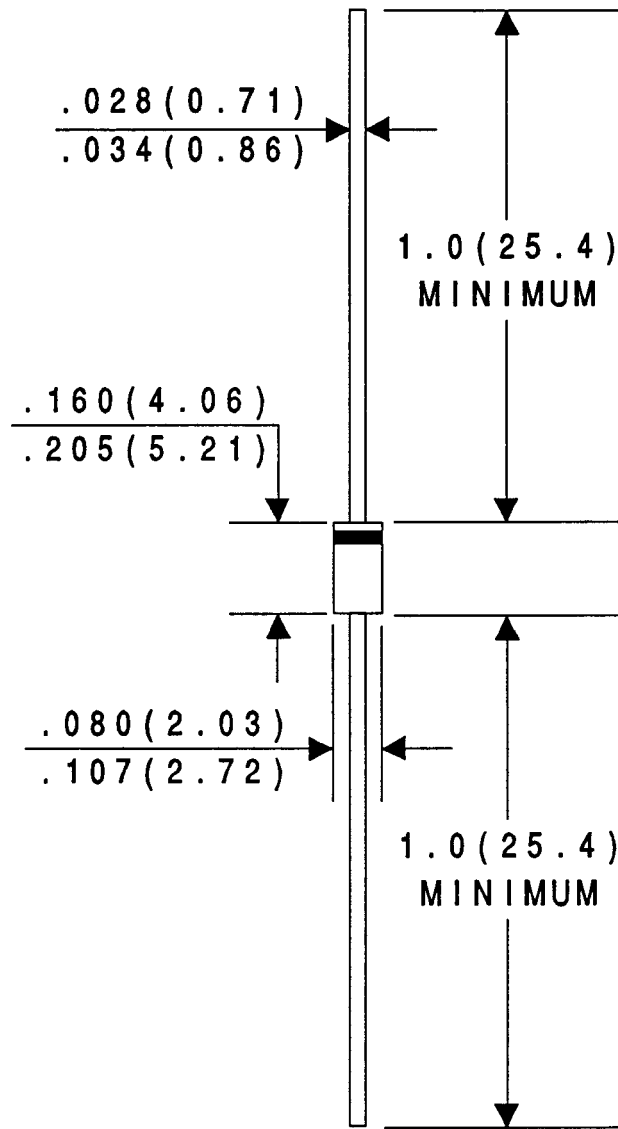
SYMBOL	1N4001	1N4002	1N4003	1N4004	1N4005	1N4006	1N4007	UNITS
	GPP	GPP	GPP	GPP	GPP	GPP	GPP	
Peak Repetitive Reverse Voltage V_{RRM}	50	100	200	400	600	800	1000	V
DC Blocking Voltage V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage $V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Forward Current @ $T_A = 75^\circ\text{C}$	I_O			1.0				A
Peak Forward Surge Current I_{FSM}				30				A
Operating and Storage Junction Temperature T_J, T_{stg}				-65 to +175				$^\circ\text{C}$
Thermal Resistance θ_{JA}				45				$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	$I_F = 1.0\text{A}$			1.1	V
I_R	$V_R = \text{Rated } V_{RRM}$			5.0	μA
I_R	$V_R = \text{Rated } V_{RRM}, T_A = 125^\circ\text{C}$			50	μA
t_{rr}	$I_F = 0.5\text{A}, I_R = 1.0\text{A}, I_{rr} = 0.25\text{A}$			2.0	μs
C_J	$V_R = 4.0\text{V}, f = 1.0\text{MHz}$		8.0		pF

(SEE REVERSE FOR MECHANICAL OUTLINE)

JEDEC DO-41 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).